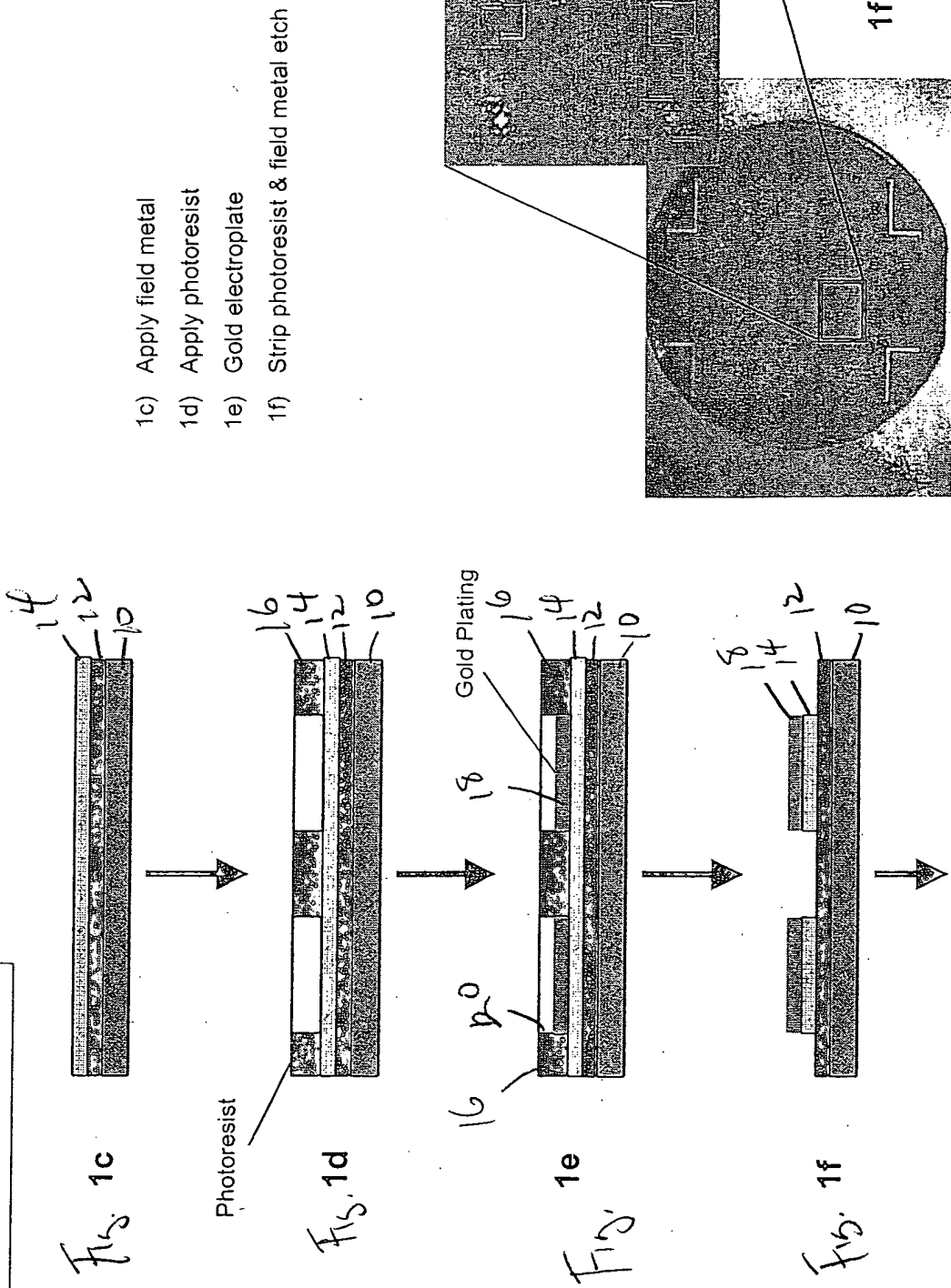


Reverse Neo Process

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- 1c) Apply field metal
- 1d) Apply photoresist
- 1e) Gold electroplate
- 1f) Strip photoresist & field metal etch

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Fig 1g

- 1g) Apply polyimide
- 1h) Apply photoresist
- 1i) Image & develop photoresist & polyimide
- 1j) Strip photoresist & cure polyimide

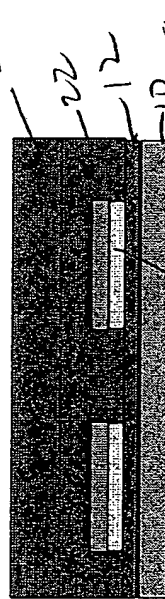


Fig 1h

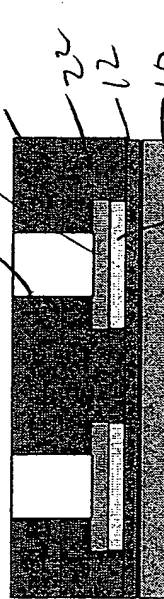


Fig 1i

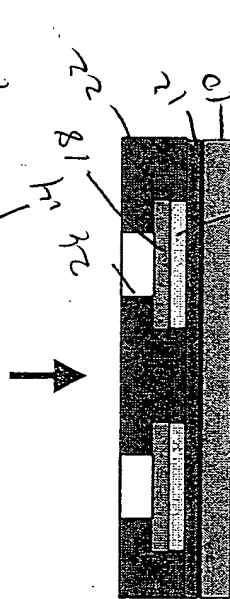


Fig 1j

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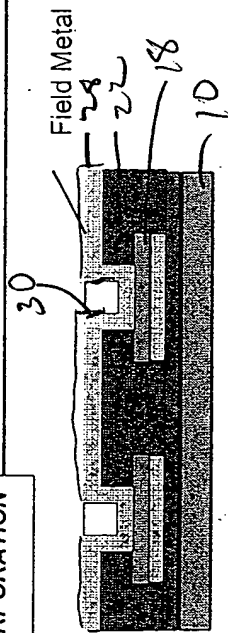


Fig. 1k



- 1k) Apply field metal
- 1l) Apply photoresist
- 1m) Image & develop photoresist. Gold electroplate
- 1n) Strip photoresist & field metal etch

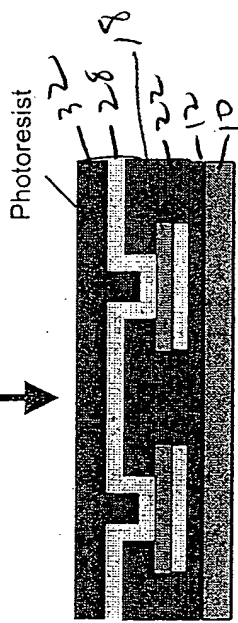


Fig. 1l

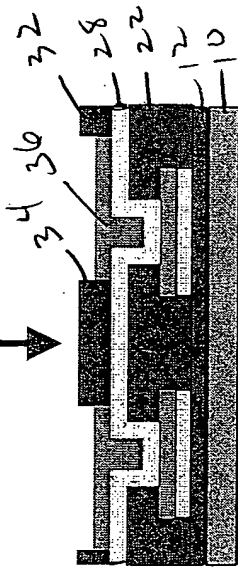


Fig. 1m

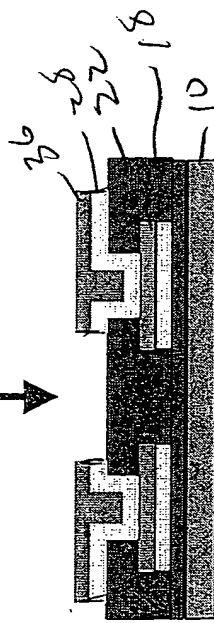


Fig. 1n

NOTE: For additional layers, steps 1g through 1n are repeated.

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Solder Bumping Of Die

Fig. 2a



- 2a) Retrieve die
- 2b) Apply underbump metalurgy
- 2c) Apply solder bump

Fig. 2b

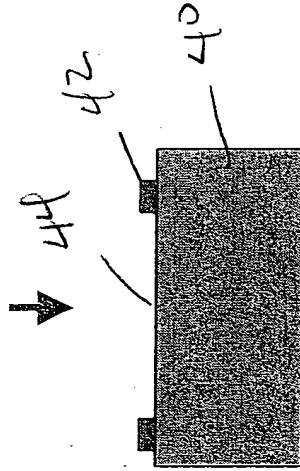
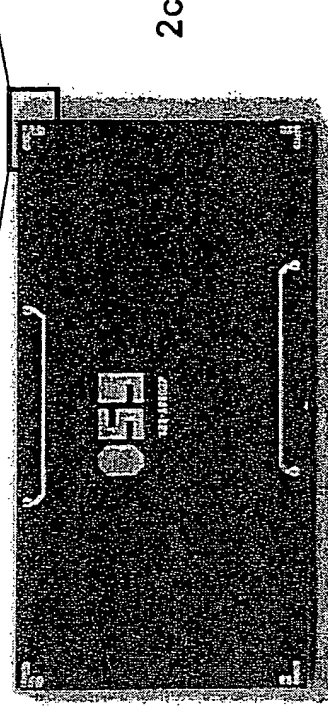
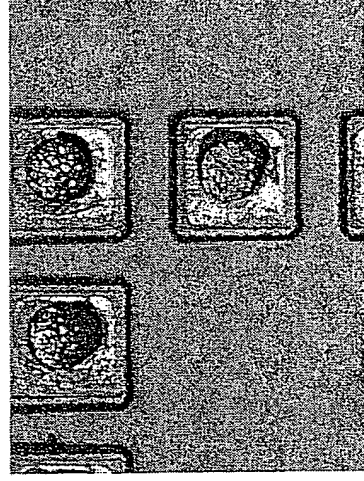
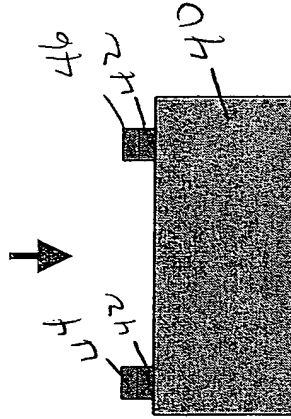


Fig. 2c

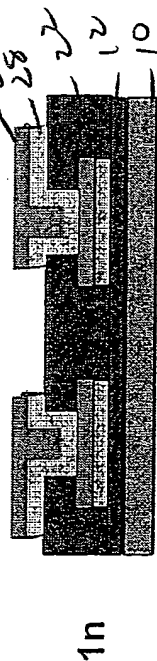


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Flip-Chip Bonding

H10.30

Retrieve substrate assembly and bumped die



12

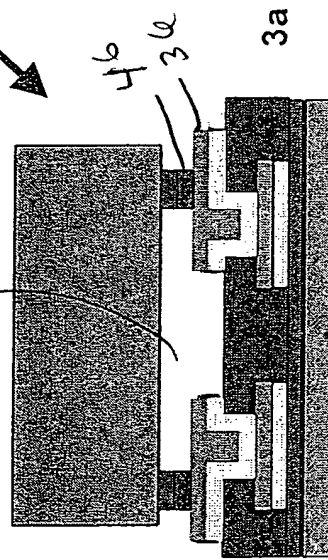
20

48

22

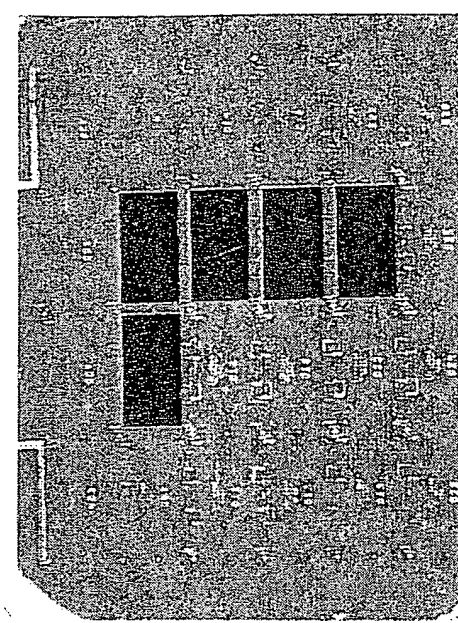
9.

3a) Flip chip bumped die to substrate



3a

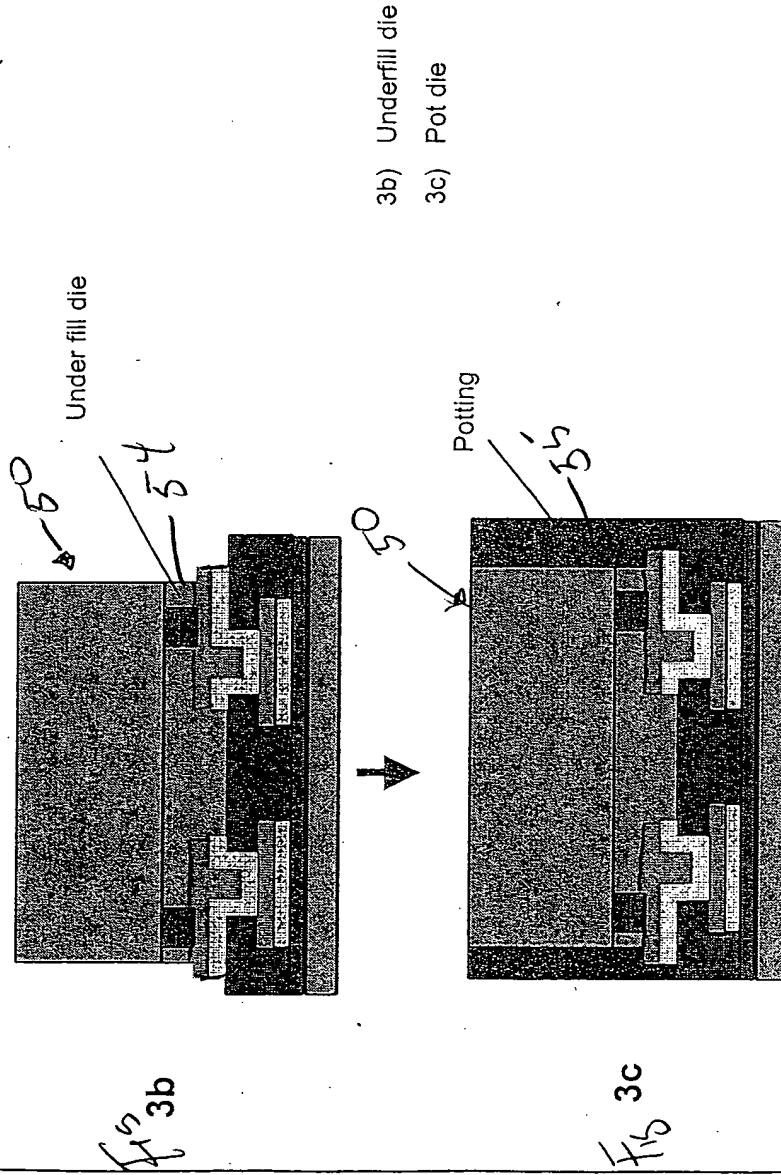
48



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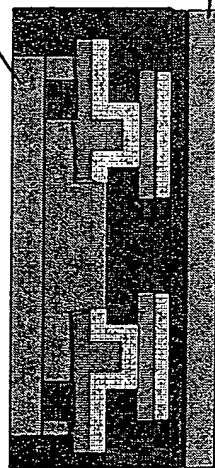


Fig. 3d

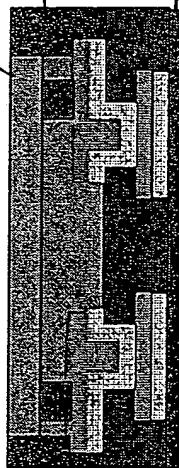


Fig. 3e

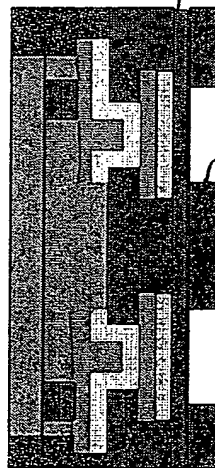
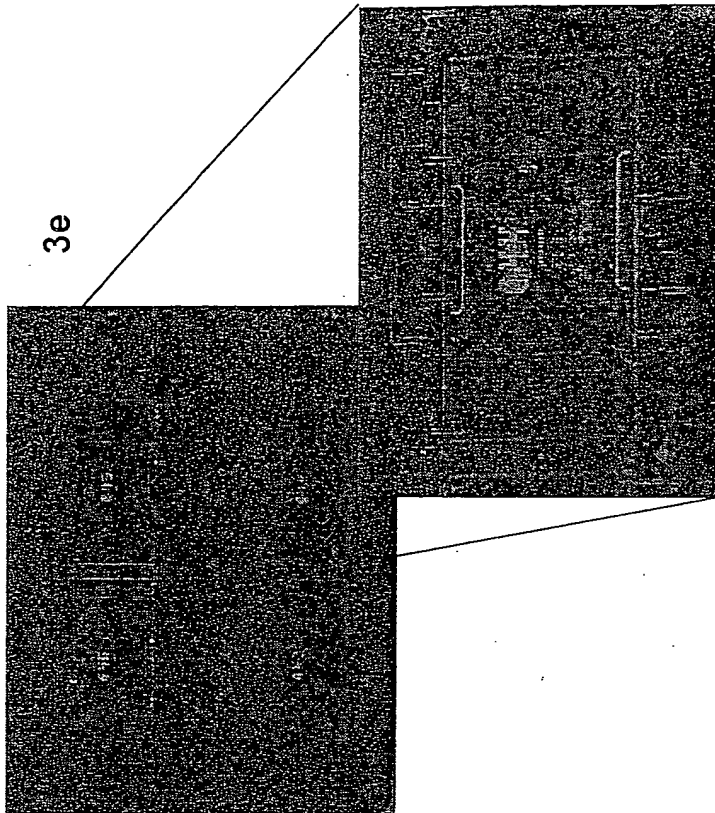


Fig. 3f

- 3d) Thin wafer
- 3e) Release wafer from aluminum substrate
- 3f) Mask wafer for test pad etch



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Reverse Neo Process

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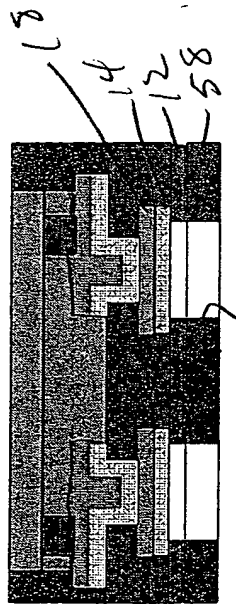


Fig 3g

- 3g) Etch polyimide to expose test pads
- 3h) Remove etch mask & test wafer
- 3i) Dice wafer

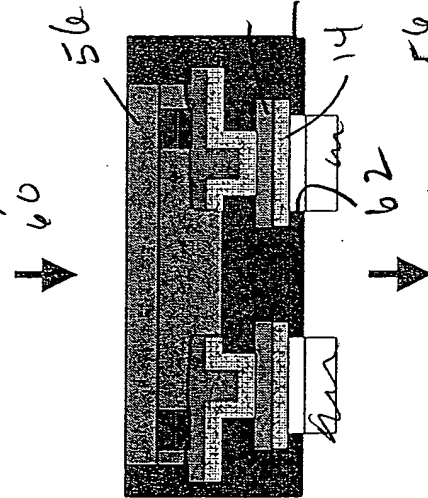


Fig 3h

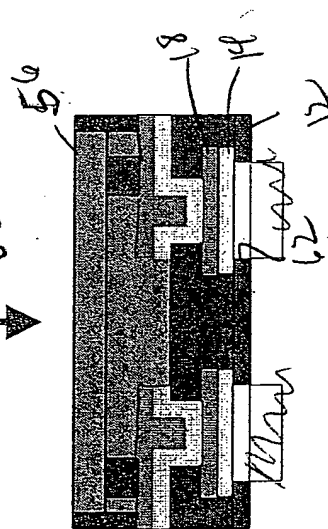
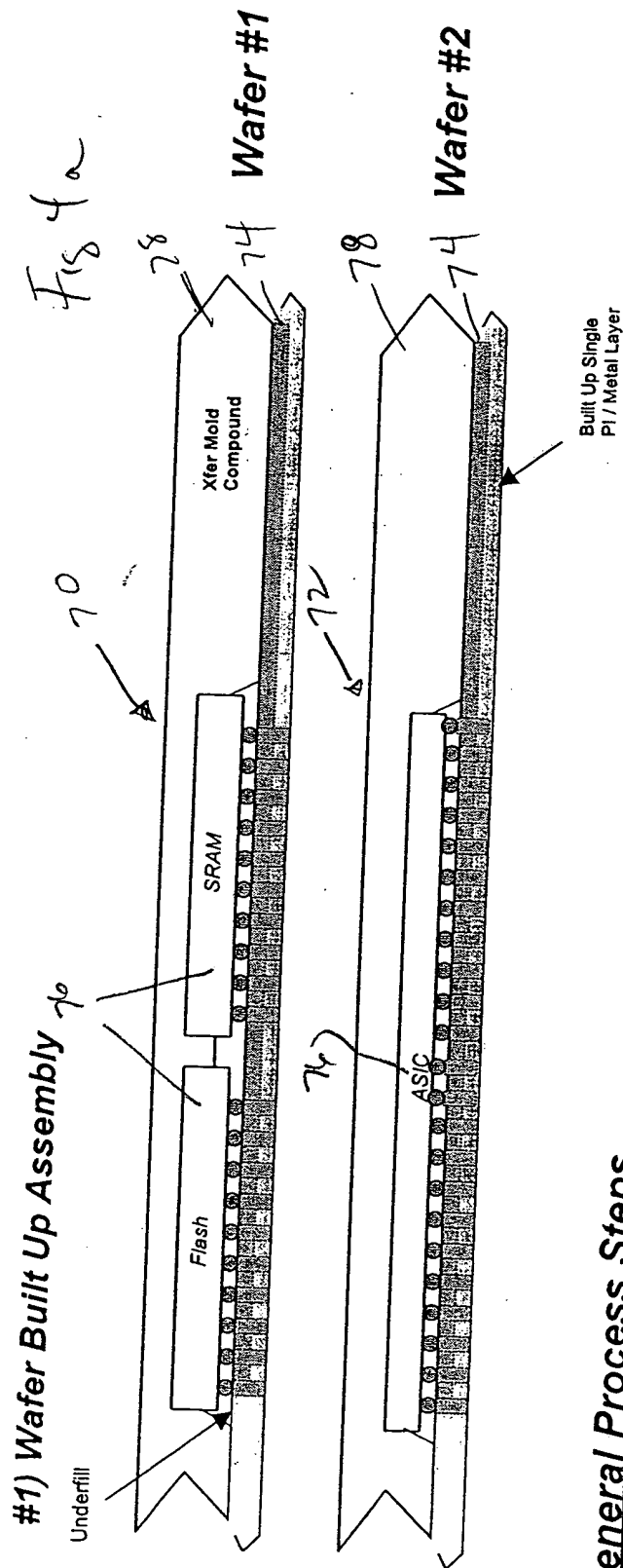


Fig 3i

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High Volume Reverse NEO Process



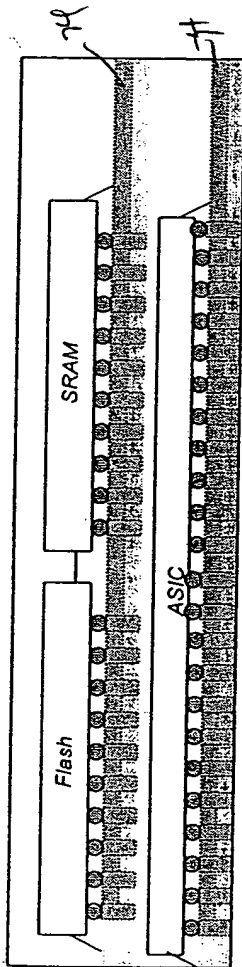
General Process Steps

- 1) Screen Print Electrically Conductive Epoxy on Built-Up Laminate Substrates
- 2) Place Flip Chip Devices
- 3) Cure Epoxy
- 4) Underfill Devices
- 5) Xfer. Mold Devices

High Volume Reverse NEO Process

2) Stacked Wafer Strip Assembly

Fig. 40-40

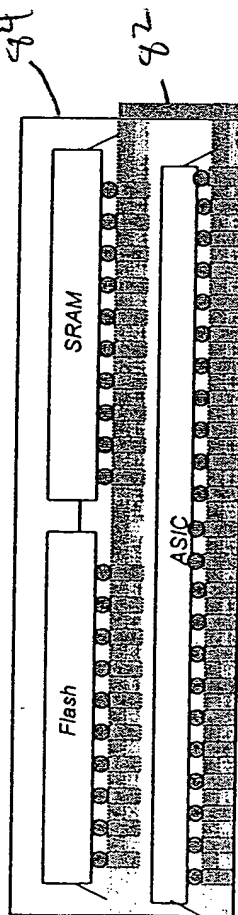


General Process Steps

- 6) Release Carrier Film from Substrate (If Required)
- 7) Attach Memory and ASIC Wafers
- 8) Cut/Saw Wafers to Strips

3) Stacked Wafer Strip Assembly

Fig. 40-40



General Process Steps

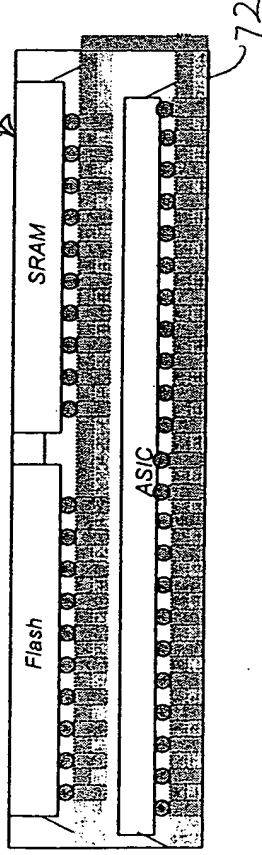
- 9) Interconnect or Bus Wafers by Metallizing Wafer Stacks

High Volume Reverse NEO Process

General Process Steps

10) Thin Stack Assembly

4) Thinned and Sawed Assembly



General Process Steps

- 11) Solder Bump Stack
- 12) Singulate (Saw) into Individual Stacks

5) Thinned and Sawed Assembly

